

HIGH SPEED CMOS TIMER

GENERAL DESCRIPTION

The ALD555 timer is a high performance monolithic timing circuit built with advanced silicon gate CMOS technology. It offers the benefits of high input impedance, thereby allowing smaller timing capacitors and longer timing cycle; high speed, with typical cycle time of 500ns; low power dissipation for battery operated environment; reduced supply current spikes, allowing smaller and lower cost decoupling capacitors. It is capable of producing accurate time delays and oscillations in both monostable and astable operation. It operates in the one-shot (monostable) mode or 50% duty cycle free running oscillation mode with a single resistor and one capacitor. The inputs and outputs are fully compatible with CMOS, NMOS or TTL logic.

There are three matched internal resistors (approximately $200 \mathrm{K}\Omega$ each) that set the threshold and trigger levels at two-thirds and one-third respectively of V+ These levels can be adjusted by using the control terminal (pin 5). When the trigger input is below the trigger level, the output is in the high state and sourcing 2mA. When threshold input is above the threshold level at the same time the trigger input is above the trigger level, the internal flip-flop is reset, the output goes to the low state and sinks up to 10mA. The reset input overrides all other inputs and when it is active (reset voltage less than 1V), the output is in the low state.

FEATURES

- Functional equivalent to NE555 with greatly expanded high and low frequency ranges
- High speed, low power, monolithic CMOS technology
- Low supply current 100μA typical
- Extremely low trigger, threshold and reset currents -- 1pA typical
- High speed operation -- 2MHz oscillation
- Low operating supply voltage 2 to 12V
- Operates in both monostable and astable modes
- Fixed 50% duty cycle or adjustable duty cycle CMOS, NMOS and TTL compatible input/output
- · High discharge sinking current (80mA)
- · Low supply current spikes

ORDERING INFORMATION

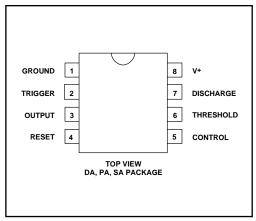
Operating Temperature Range *							
-55°C to +125°C	0°C to +70°C	0°C to +70°C					
8-Pin CERDIP Package	8-Pin Small Outline Package (SOIC)	8-Pin Plastic Dip Package					
ALD555 DA	ALD555 SA	ALD555 PA					

^{*} Contact factory for industrial temperature range

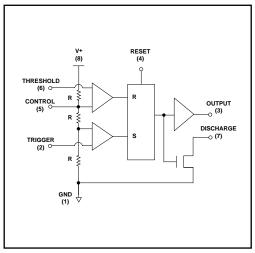
APPLICATIONS

- High speed one-shot (monostable) pulse generation
- · Precision timing
- · Sequential timing
- Long delay timer
- Pulse width and pulse position modulation
- · Missing pulse detector
- Frequency divider

PIN CONFIGURATION



BLOCK DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Supply voltage, V+	13.2V
Input voltage range ————————————————————————————————————	-0.3V to V+ +0.3V
Power dissipation ————————————————————————————————————	600 mW
Operating temperature range PA,SA package	0°C to +70°C
DA package	
Storage temperature range	65°C to +150°C
Lead temperature, 10 seconds	+260°C

OPERATING ELECTRICAL CHARACTERISTICS $T_A = 25$ °C V+= +5V unless otherwise specified

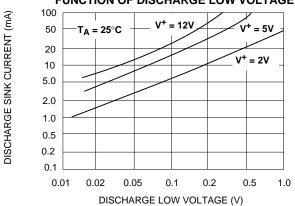
Parameter	Symbol	Min	Тур	Max	Unit	Test Conditions
Supply Voltage	V+	2		12	V	
Supply Current	IS		100	180	μΑ	Outputs Unloaded
Timing error / Astable mode Initial Accuracy	t _{err}		1.0	2.2	%	C = 0.1μF
Drift with Temperature ¹ Drift with Supply Voltage ¹	Δt/ΔT Δt/ΔV+		10.0 0.1		ppm/°C %/V	$R_A = 1KΩ$ $R_B = 1KΩ$
Threshold Voltage	V _{TH}	3.273	3.333	3.393	V	
Trigger Voltage	V _{TRIG}	1.607	1.667	1.737	V	
Trigger Current ²	I _{TRIG}		.001	0.2	nA	
Reset Voltage	V _{RST}	0.4	0.7	1.0	V	
Reset Current ²	IRST		.001	0.2	nA	
Threshold Current ²	I _{TH}		.001	0.2	nA	
Control Voltage Level	V _{CONT}	3.273	3.333	3.393	V	
Output Voltage Drop (Low)	V _{OL}		0.2	0.4	V	I _{SINK} = 10mA
Output Voltage Drop (High)	V _{OH}			4.2	V	I _{SOURCE} = -2mA
Rise Time of Output ¹	t _r		15	30	ns	$R_L = 10M\Omega$
Fall Time of Output ¹	t _f		10	20	ns	C _L = 10pF
Discharge Transistor Leakage Current	I _{DL}		.01		nA	
Discharge Voltage Drop	V _{DISC}		0.5 0.2	1.0 0.4	V V	I DISCHARGE = 80mA I DISCHARGE = 30mA
Maximum Frequency Astable Mode	fMAX	1.4	2		MHz	$R_{A} = 470\Omega$ $R_{B} = 200\Omega$ $C_{T} = 200pF$

Notes: ¹ Sample tested parameters. ² Consists of junction leakage currents with strong temperature dependence.

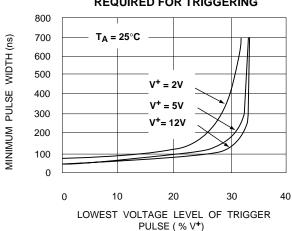
TYPICAL PERFORMANCE CHARACTERISTICS

FREQUENCY CHANGE (%)

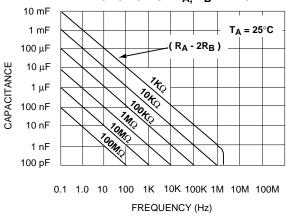
DISCHARGE OUTPUT SINK CURRENT AS A FUNCTION OF DISCHARGE LOW VOLTAGE



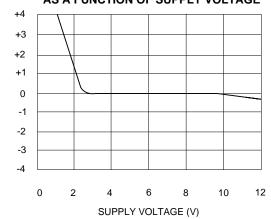
MINIMUM PULSE WIDTH REQUIRED FOR TRIGGERING



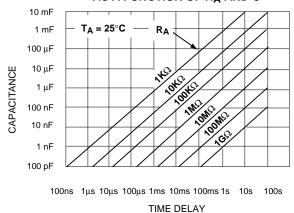
FREE RUNNING FREQUENCY AS A FUNCTION OF RA, RB AND C



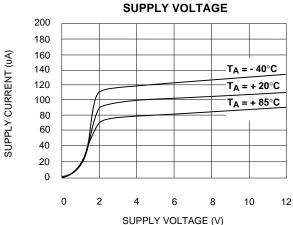
FREQUENCY CHANGE IN THE ASTABLE MODE AS A FUNCTION OF SUPPLY VOLTAGE



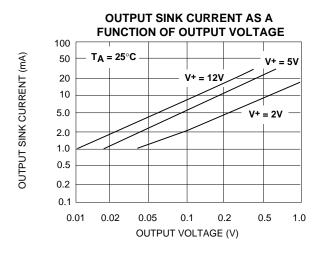
TIME DELAY IN THE MONOSTABLE MODE AS A FUNCTION OF $R_{\mbox{\scriptsize A}}$ AND C



SUPPLY CURRENT AS A FUNCTION OF



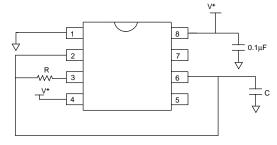
TYPICAL PERFORMANCE CHARACTERISTICS



OUTPUT SOURCE CURRENT AS A FUNCTION OF OUTPUT VOLTAGE -0.1 OUTPUT SOURCE CURRENT (mA) -0.2 V + = 2V-0.5 -1.0 -2.0 -5.0 -10 -20 -50 -100 -0.1 -0.05 -1.0 -0.5 -0.2 -0.02 -0.01 OUTPUT VOLTAGE (V) (REFERENCED TO V+)

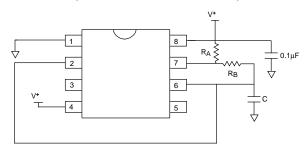
TYPICAL APPLICATIONS

ASTABLE MODE OPERATION 50% DUTY CYCLE



Frequency f = 1/ (1.4 Rc)

ASTABLE MODE OPERATION (FREE RUNNING OSCILLATOR)



Frequency f = 1.46 / (RA + 2RB)C Duty Cycle DC = RB / (RA + 2RB)

MONOSTABLE MODE OPERATION (ONE SHOT PULSE) Pulse Delay td = 1.1 R_C

